

IN THE CLAIMS:

Each claim that remains pending and under consideration in the above-referenced application is reproduced below, in clean form, for the sake of clarity. In addition, a marked-up version of each amended claim is enclosed herewith to clearly show each change that has been made thereto.

Please enter the claims as follows:

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1. (Amended four times) A method of modifying a semiconductor die, comprising: providing at least one semiconductor die having an active surface; and forming on or securing to said active surface at least one stabilizer comprising a dielectric material such that said at least one stabilizer protrudes from said active surface, said at least one stabilizer being configured to space said at least one semiconductor die a substantially fixed distance apart from a higher-level substrate when disposed active surface-down over said higher-level substrate.

2. The method of claim 1, wherein said forming said at least one stabilizer comprises forming a plurality of stabilizers.

3. The method of claim 2, wherein said forming said plurality of stabilizers comprises forming at least one stabilizer of said plurality of stabilizers adjacent at least one corner of said active surface.

4. The method of claim 2, wherein said forming said plurality of stabilizers comprises forming at least two stabilizers adjacent opposite peripheral edges of said active surface.

5. The method of claim 2, wherein said forming said plurality of stabilizers comprises forming selected ones of said plurality of stabilizers to have a height that defines a substantially consistent die-to-substrate distance.

Sub E 6. The method of claim 1, wherein said forming said at least one stabilizer comprises forming said at least one stabilizer from photoimageable material.

7. The method of claim 6, wherein said forming said at least one stabilizer comprises forming said at least one stabilizer as at least two superimposed, contiguous, mutually adhered layers of material.

D1 8. (Amended) The method of claim 1, wherein said providing comprises providing at least one semiconductor die having a sealing material on an active surface thereof and wherein said forming comprises forming said at least one stabilizer to be securable to said sealing material.

9. (Amended) The method of claim 1, wherein said providing comprises providing a semiconductor wafer including a plurality of semiconductor dice.

10. The method of claim 1, further comprising adhering said at least one stabilizer to said active surface.

11. The method of claim 1, wherein said forming said at least one stabilizer comprises applying a layer of insulative material on said active surface and patterning said layer.

12. The method of claim 1, wherein said forming said at least one stabilizer comprises applying a layer of photoresist material on said active surface and patterning said layer.

13. (Twice amended) The method of claim 1, further comprising introducing an encapsulant material between said at least one semiconductor die and said substrate.

Sub E1 14. The method of claim 1, wherein said forming said at least one stabilizer comprises positioning said at least one stabilizer on said active surface so as to avoid contact with conductive traces on a carrier substrate.

15. (Amended) The method of claim 1, further comprising disposing at least one conductive structure on at least one bond pad of said at least one semiconductor die.

16. The method of claim 15, wherein said disposing comprises forming a solder bump on said at least one bond pad.

D1 17. (Previously amended) The method of claim 15, wherein said disposing comprises applying one of a conductive pillar, a conductor filled epoxy pillar, and a structure of z-axis elastomer to said at least one bond pad.

18. (Amended four times) A method of modifying a semiconductor device component, comprising:
providing at least one semiconductor substrate with contact pads on an active surface thereof;
and
sequentially forming on said active surface at least one stabilizer having a plurality of superimposed, contiguous, mutually adhered layers of photopolymer, said at least one stabilizer being configured to at least partially stabilize an orientation of the semiconductor device component upon being disposed active surface-down over a higher-level substrate.

19. (Amended four times) A method of modifying a semiconductor device component, comprising:
placing at least one semiconductor substrate having an active surface with contact pads exposed thereon in a horizontal plane;
recognizing a location and orientation of said at least one substrate;

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 stereolithographically forming on said active surface, between one of said contact pads and a peripheral edge of said at least one substrate, at least one stabilizer comprising at least one layer of an electrically nonconductive semisolid material.

20. (Previously amended) The method of claim 19, further comprising storing data including at least one physical parameter of said at least one substrate in computer memory, and using the stored data in conjunction with a machine vision system to recognize said location and orientation of said at least one substrate and to form said at least one stabilizer thereon.

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 21. The method of claim 20, further including in computer memory at least one parameter of another semiconductor device component to which said at least one substrate is to be attached.

22. (Previously amended) The method of claim 20, further comprising using stored data, in conjunction with said machine vision system, to selectively form said at least one layer of semisolid material stereolithographically on at least one portion of said active surface of said at least one substrate.

23. The method of claim 20, further including securing said at least one substrate to a carrier prior to placing said at least one substrate in said horizontal plane.

36. (Amended four times) A method for electrically bonding a semiconductor device component having a surface and conductive structures protruding from said surface to a substrate having contacts positioned correspondingly to said conductive structures, said method comprising:
forming at least one stabilizer structure comprising a dielectric material on at least one of said surface and said substrate for disposal between said surface and said substrate;
inverting and positioning said semiconductor device component on said substrate to contact said conductive structures to corresponding contacts; and
bonding said conductive structures to the corresponding contacts.

Sub E1 37. (Previously three times amended) The method of claim 36, wherein said forming at least one stabilizer structure comprises forming said at least one stabilizer structure to have a height less than a minimum distance said conductive structures protrude from said surface.

38. (Previously three times amended) The method of claim 36, wherein said forming at least one stabilizer structure comprises forming said at least one stabilizer structure to space said surface from said substrate a distance greater than a minimum distance at least one of said conductive structures protrudes from said surface.

D1 39. (Previously three times amended) The method of claim 38, wherein said bonding comprises employing said at least one stabilizer structure to lengthen at least one of said conductive structures.

40. (Previously three times amended) The method of claim 36, wherein said forming at least one stabilizer structure comprises configuring said at least one stabilizer structure to be positioned between a periphery of said surface of said semiconductor device component and said conductive structures.

41. (Twice amended) A method of modifying a semiconductor die, comprising:
providing at least one semiconductor die having an active surface with contact pads exposed thereon;
applying a layer of a partially uncured photopolymer to said semiconductor; and
stereolithographically forming on said semiconductor, between one of said contact pads and a peripheral edge of said semiconductor, at least one stabilizer securable to said active surface so as to protrude from said active surface, said at least one stabilizer being a structure configured to at least partially stabilize an orientation of said at least one semiconductor die when disposed active surface-down over a higher-level substrate.

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42. The method of claim 41, wherein said forming said at least one stabilizer comprises forming a plurality of stabilizers.

43. The method of claim 42, wherein said forming said plurality of stabilizers comprises forming at least one stabilizer of said plurality of stabilizers adjacent at least one corner of said active surface.

44. The method of claim 42, wherein said forming said plurality of stabilizers comprises forming selected ones of said plurality of stabilizers to have a height that defines a substantially consistent die-to-substrate distance.

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45. (Amended) The method of claim 41, wherein said providing comprises providing a semiconductor wafer including a plurality of semiconductor dice.

46. (Amended) The method of claim 41, further comprising introducing an encapsulant material between said at least one semiconductor die and said substrate.

47. The method of claim 41, wherein said forming said at least one stabilizer comprises positioning said at least one stabilizer on said active surface so as to avoid contact with conductive traces on a carrier substrate.

48. (Amended) The method of claim 41, further comprising disposing at least one conductive structure on at least one bond pad of said at least one semiconductor die.

49. The method of claim 48, wherein said disposing comprises forming a solder bump on said at least one bond pad.